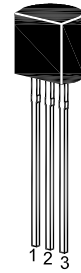


2SA1016

PNP Silicon Epitaxial Planar Transistor

High voltage amplifier applications

The transistor is subdivided into three groups F, G and H, according to its DC current gain.



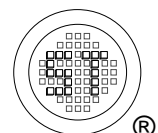
1. Emitter 2. Collector 3. Base
TO-92 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	120	V
Collector Emitter Voltage	$-V_{CEO}$	100	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	50	mA
Collector Current (Pulse)	$-I_{CP}$	100	mA
Collector Dissipation	P_{tot}	400	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $-V_{CE} = 6\text{ V}$, $-I_C = 1\text{ mA}$	Current Gain Group F	h_{FE}	160	-	320	-
	G	h_{FE}	280	-	560	-
	H	h_{FE}	480	-	960	-
Collector Base Breakdown Voltage at $-I_C = 10\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	120	-	-	V	
Collector Emitter Breakdown Voltage at $-I_C = 1\text{ mA}$	$-V_{(BR)CEO}$	100	-	-	V	
Emitter Base Breakdown Voltage at $-I_E = 10\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	5	-	-	V	
Collector Base Cutoff Current at $-V_{CB} = 80\text{ V}$	$-I_{CBO}$	-	-	1	μA	
Emitter Base Cutoff Current at $-V_{EB} = 4\text{ V}$	$-I_{EBO}$	-	-	1	μA	
Collector Emitter Saturation Voltage at $-I_C = 10\text{ mA}$, $-I_B = 1\text{ mA}$	$-V_{CE(sat)}$	-	-	0.5	V	
Gain Bandwidth Product at $-V_{CE} = 6\text{ V}$, $-I_C = 1\text{ mA}$	f_T	-	110	-	MHz	
Output Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{OB}	-	2.2	-	pF	



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